

<b>Notice of References Cited</b>			Application/Control No. 10/532,782	Applicant(s)/Patent Under Reexamination KUMAKURA ET AL.
			Examiner Jonathan C. Langman	Art Unit 1775      Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,741,724	04-1998	Ramdani et al.	438/46
*	B	US-6,362,515	03-2002	Hayakawa, Toshiro	257/639
*	C	US-6,744,076	06-2004	Fukuyama et al.	257/103
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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	N					
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages
	U	Cho et al., "Effects of N+-implanted sapphire (0001) substrate on GaN epilayer". Journal of Crystal Growth, Volume 236, Issue 4, March 2002, Pages 538-544
	V	Liu et al., "Substrates for gallium nitride epitaxy". Materials Science and Engineering: R: Reports, Volume 37, Issue 3, 30 April 2002, Pages 61-127.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.